



Modelling signal digitisation for test calorimeters: the CALICE experience

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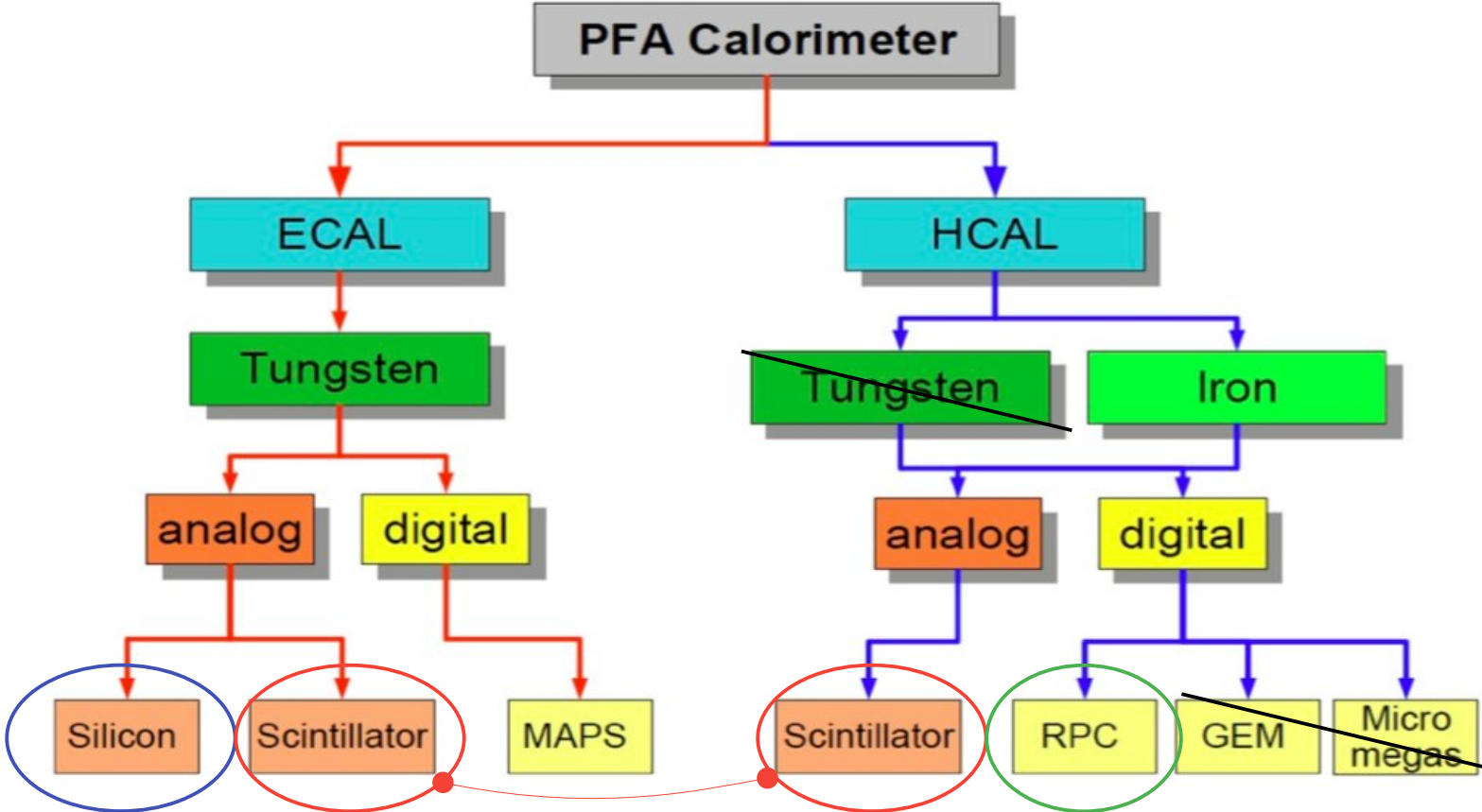
Institut Polytechnique de Paris

LMR

***FCC Week, 23-26/06/2023
Krakow***

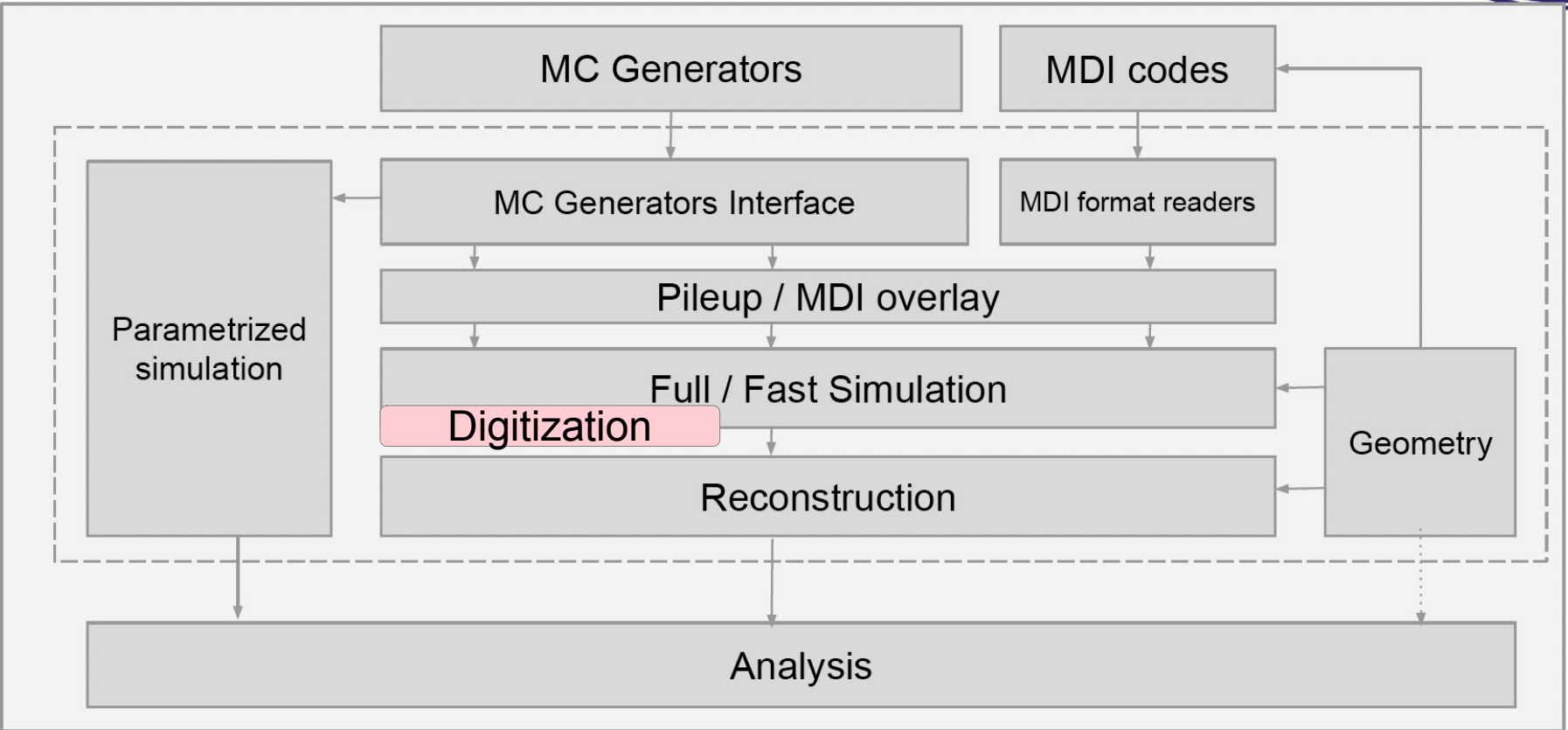


CALICE Collaboration & Prototypes



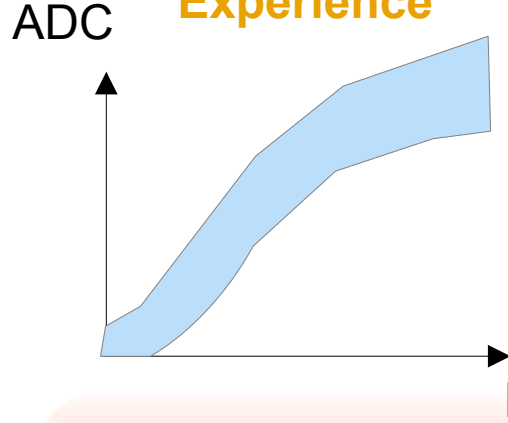
MAPS (FoCal) missing in this talks

What is digitization ?



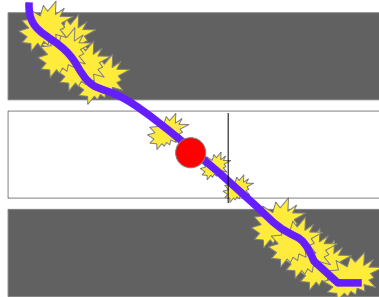
Problems:

Experience



E-t :
Saturations
non-linearities
(sensor, elec)
Statistics
Noise
Thresholds

Ecell



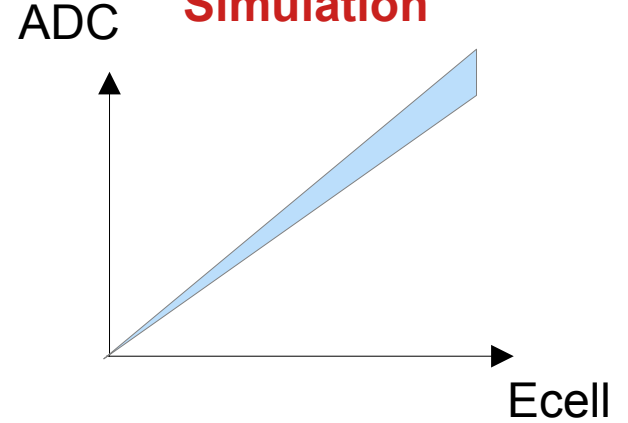
Sampling calorimeters

Mapping
(in)Efficiency
X-talk

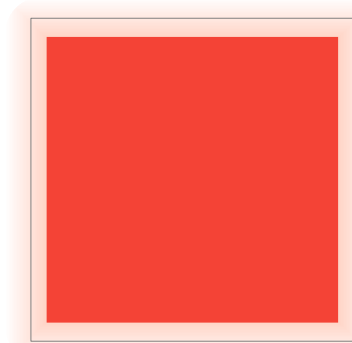
x

E-t
Physics list
Thresholds
Steps

Simulation



y



x

Mapping
Signal sharing

Short-comings

in-cell non-linear effects

- Geometric efficiency, losses

ALL

- Field/Efficiency maps
- Saturation
 - Scint: Birk's law
 - Gas
- SiPM: stat / inefficiencies
- Non-poissonian statistics
 - Si, IAr : Fano factor

Electronics non-linearities

- Energy
 - LE : (Electronics) Noises, Threshold effects
 - HE: Saturation
- Time
 - Time-slew (method dependant : ToA, CFD, Shaping)
 - Precision

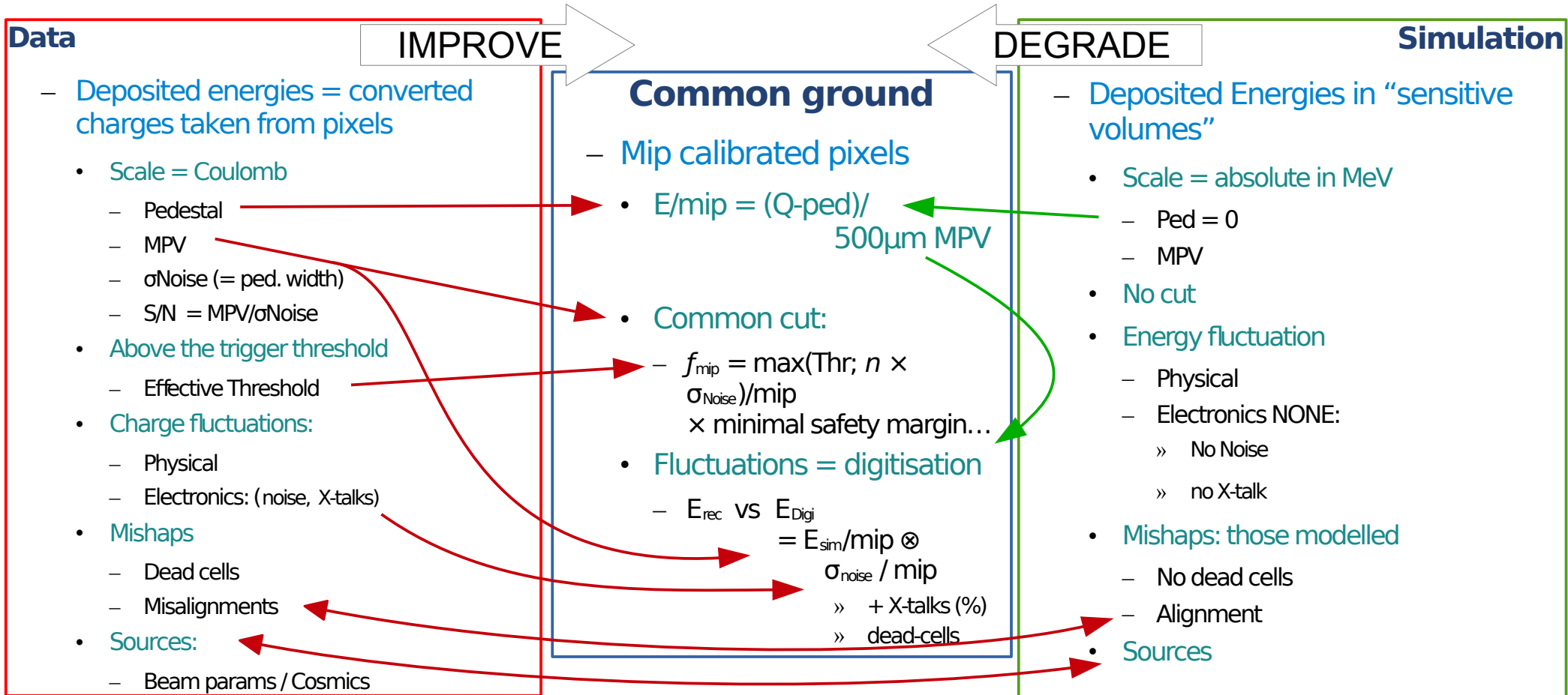
inter-cell

- X-talk
 - SDHCAL = multiplicity

Pile-ups

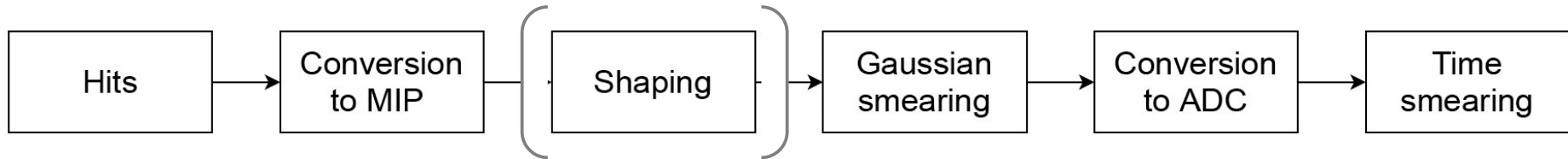
- Multiple hits
 - Time precision

Data vs Simulation (Silicon example)



Digitization: E, t space

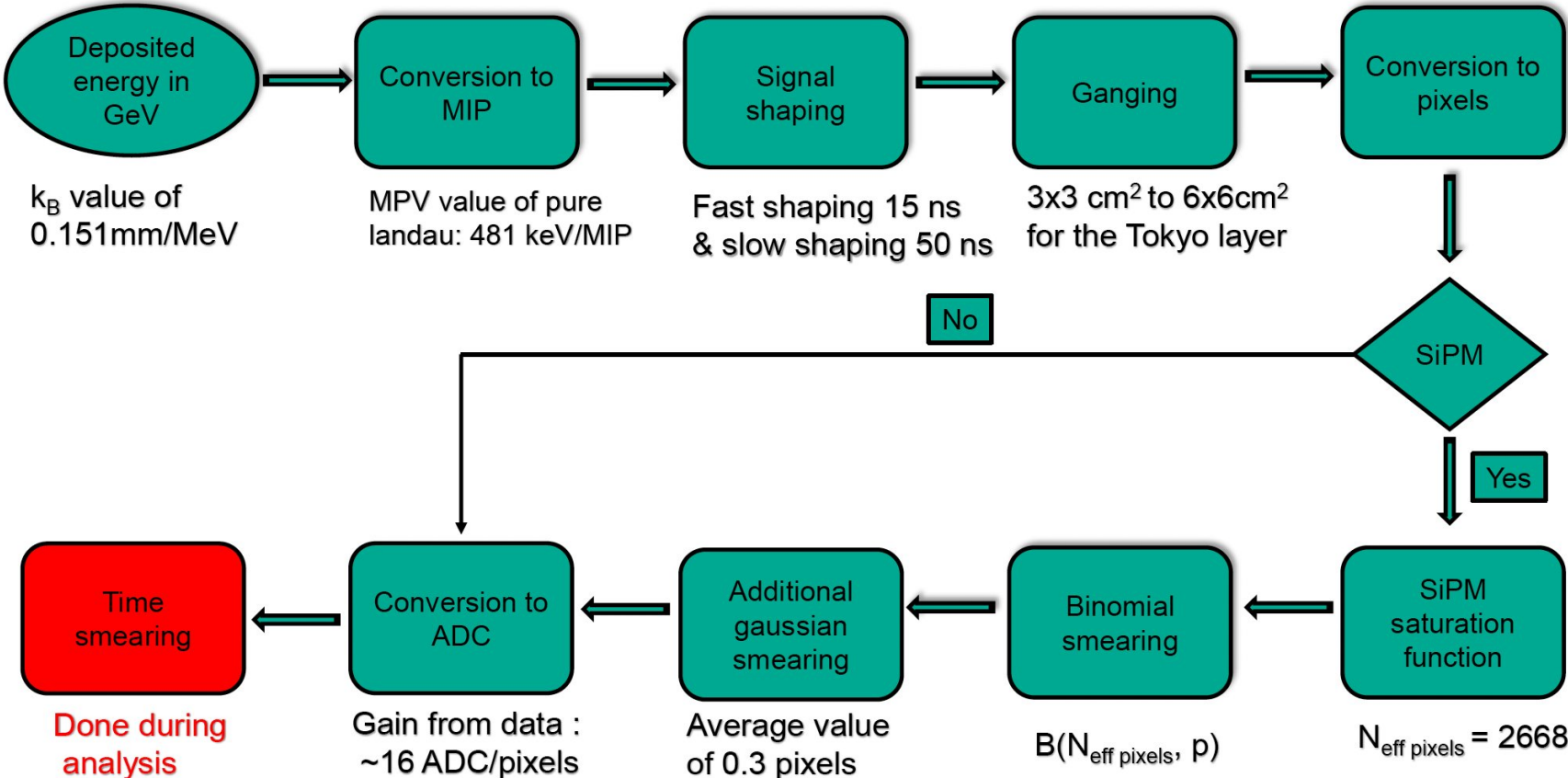
Raw simulation \Rightarrow info. resembling detector output, including readout effects



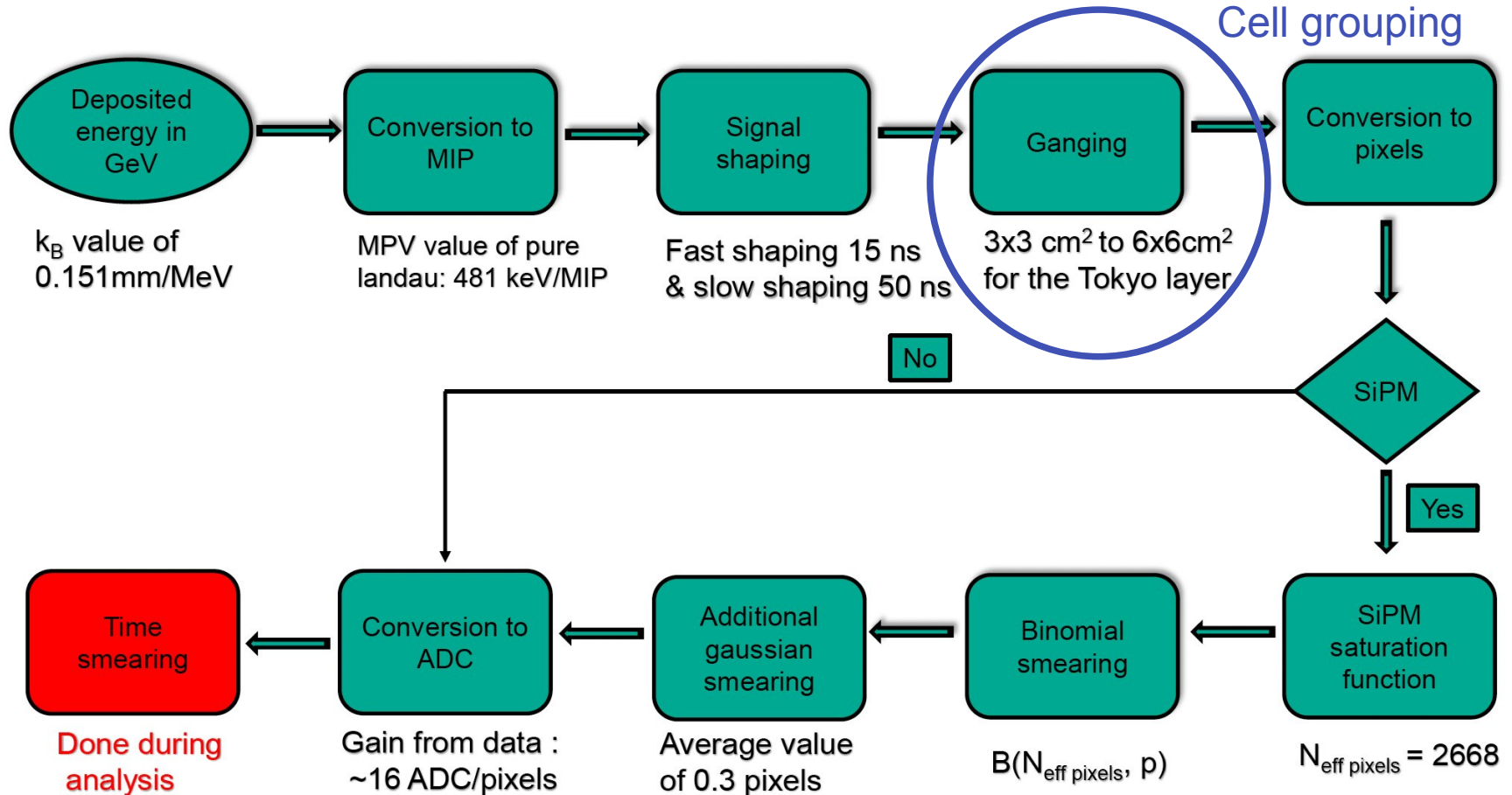
- Hits: starting point from raw simulation.
- Map energy deposited to MIP scale.
- Simulate pulse shaping in the readout electronics + saturation effects.
- Add smearing: noise term in detector cells/readout.
- Conversion to ADC, time smearing (tbd)
- (Masking at any point.)

AHCAL Digi

Light yield determined from data



Scint. Digi → ScECAL & AHCAL



Scintillator's

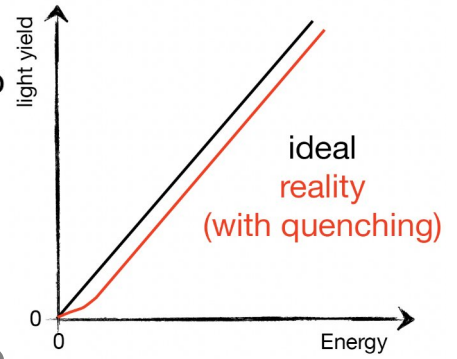
Deposited energy in GeV & conversion to MIP

Simulations of energy depositions in scintillators have to account for quenching effects giving rise to non-linear light yield per unit length (dL/dx) at high ionization densities (dE/dx)

- Birks' law describes this effect with:

$$\frac{dL}{dx} = \frac{\left(S * \frac{dE}{dx}\right)}{1 + k_B * \frac{dE}{dx}}$$

- The AHCAL simulations use the Geant4 implementation of Birks' law with a Birks coefficient of $k_B = 0.151 \text{ mm/MeV}$ https://agenda.linearcollider.org/event/4776/contributions/19855/attachments/16078/26247/CALICE_Birks.pdf



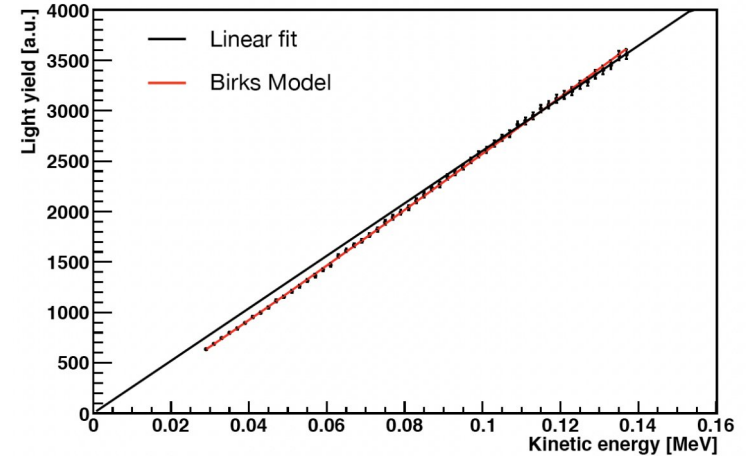
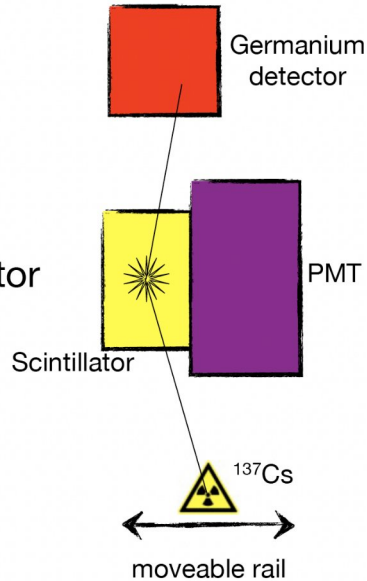
“Digi in G4”
- Birk's law
- (Light tracking)

Depends on
- Scintillator type
- Simulation step size

Experimental Setup (MPIK Heidelberg)

- PMT measures light yield
- Germanium detector measures Energy of Compton scattered photon E_{Ge}
- Coincidence trigger PMT and Ge-detector
- Measured energy range of electrons $\sim 30 - 140$ keV
- Thanks to Christoph Aberle and Stefan Wagner for the ability to use the setup
- Detailed setup description in [1]

$$E_{e^-} = 662 \text{ keV} - E_{Ge}$$



Fit function:

$$LY \approx \sum_{i=1}^{R/\delta x} \frac{S \cdot \frac{dE}{dx}(E_i)}{1 + kB \cdot \frac{dE}{dx}(E_i)} \delta x$$

Small step-size:

$$\frac{dE}{dx}(E_1) \frac{dE}{dx}(E_2) \dots \frac{dE}{dx}(E_8) \rightarrow LY_1$$

Long step-size:

$$\frac{dE}{dx}(E_1) \rightarrow LY_2$$

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Data generation

Particle type (e.g. proton)
 $kB = 0.0151 \text{ cm/MeV}$
 $S = 29807 \text{ a.u.}$



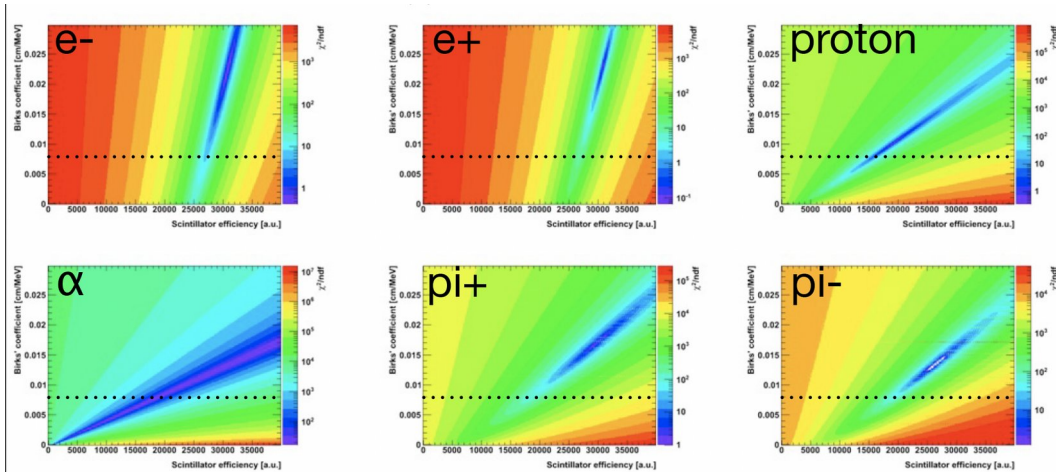
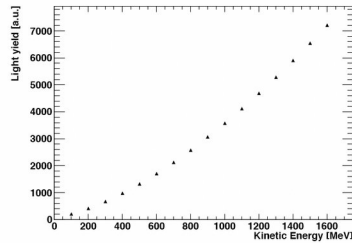
GEANT4
small step-size (α, ρ)
large production cut P_{cut}

chi squared distribution

GEANT4
default α, ρ, P_{cut}



"artificial"
 data set

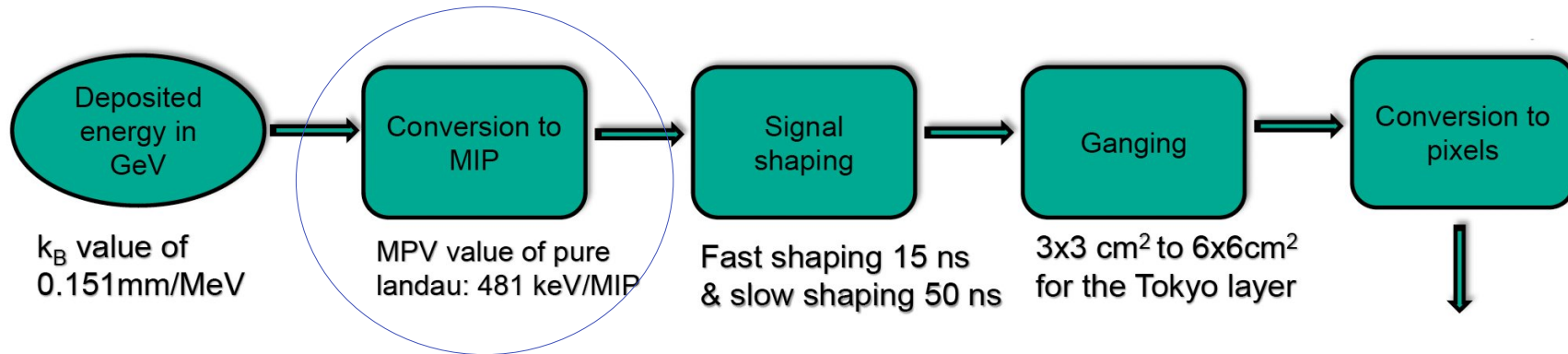


Different possibilities to combine results:
 - Common kB, S for all particles
 - Particle specific kB , but common S

..... current kB
 0.007943 cm/MeV

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AHCAL Scintillator's



Deposited energy in GeV & conversion to MIP

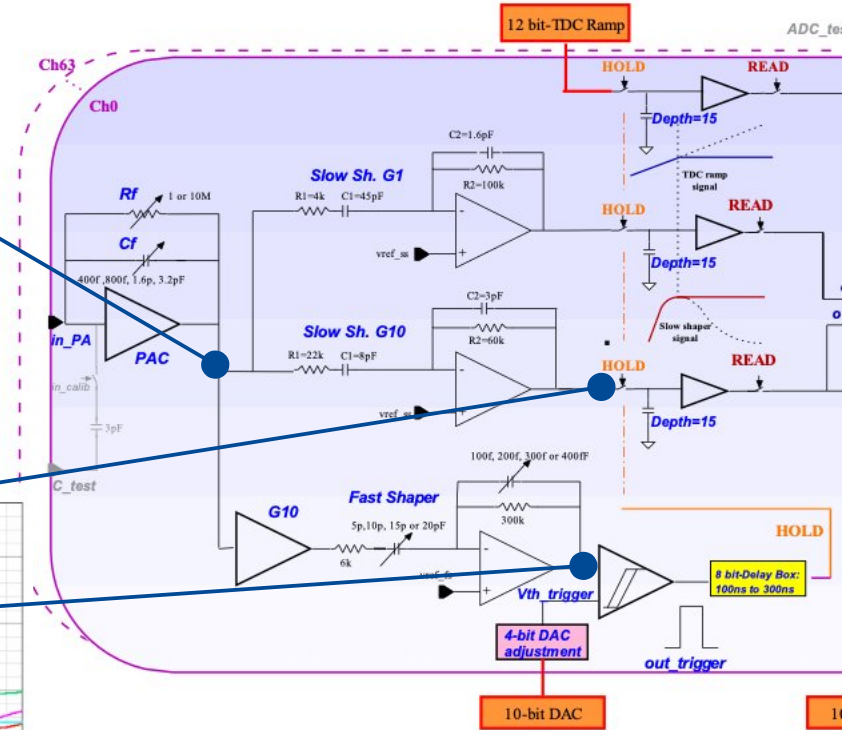
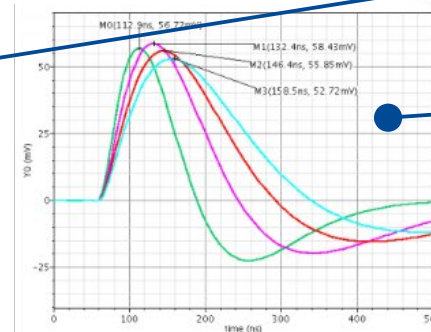
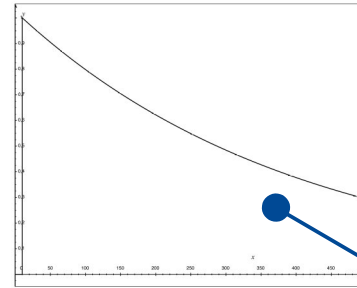
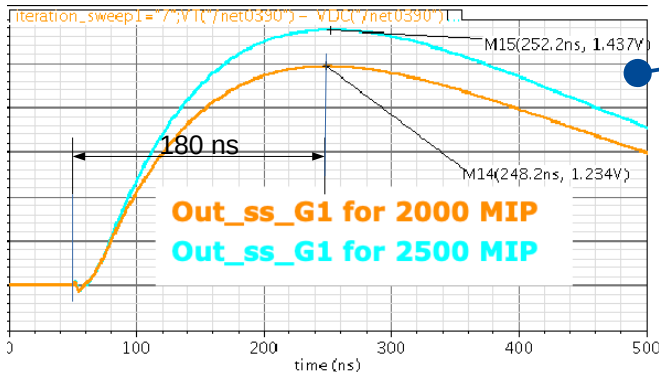
MIP2GeV is extracted from simulation by projected 40 GeV muons perpendicular on the AHCAL tile

- The MIP distribution is fitted with Landau and the position is centered around unity
- The MPV value used as the **MIP2GeV factor**. The value is **481keV/MIP**

Shaping of the SKIROC2

Signal path in each channel:

- 1 pre-Amp =
 - integrator with $\tau_i \sim 0.4\text{--}32 \mu\text{s}$
- Fast Shaper
 - CR-RC^(1~2) with τ_i and $\tau_d \sim 30\text{--}120 \text{ ns}$
- Slow Shapers
 - CR-RC^(1~2) with τ_i and $\tau_d = 180 \text{ ns}$

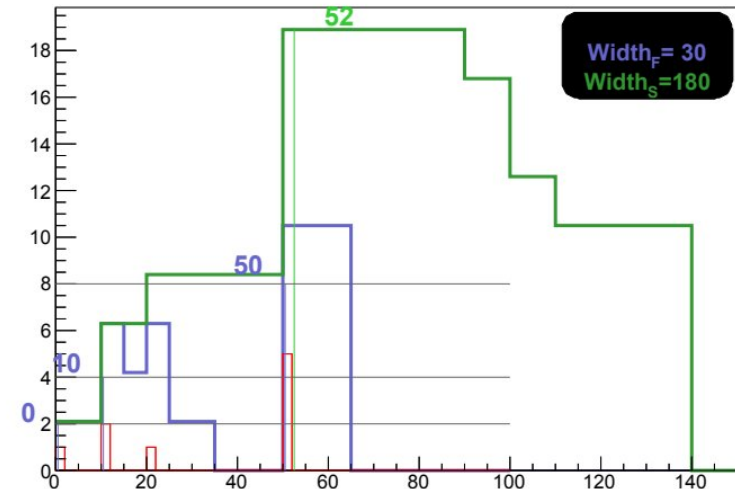
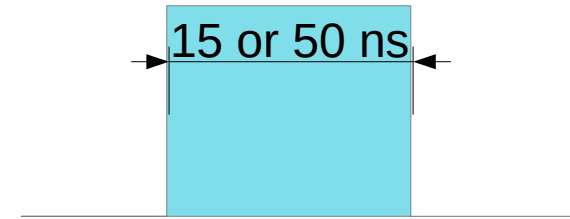


Scint : Signal shaping

Simulating Spiroc2E timestamping and energy measurement

- The energy sum of the sub-hits in a cell are integrated over a sliding time window of 50ns
- The 15ns (fast shaper) is introduced to know if the energy deposited in the cell go over threshold
- Then the energy is integrated over 50 ns (slow shaper)
- MIPThr of 0.5 in the ASIC has currently been ignored in this step. Such a cut should be present after all smearing

Equivalent to a «Heaviside shaping»



SiPM effects

Ecell / MIPs → Ecell / photon (pixel)

- Using Light Yield values from data
- Cell wise

Saturation function:

- Smearred with a binomial distribution to model the statistical process of photon detection
 - The number of fired pixels p is random from $B(N_{eff} \text{ pixels}, p)$, which has input parameters:
 - the number of effective pixels of the SiPMs ($N_{effpixels}$) and the probability p that a pixel is fired

Additional gaussian smearing:

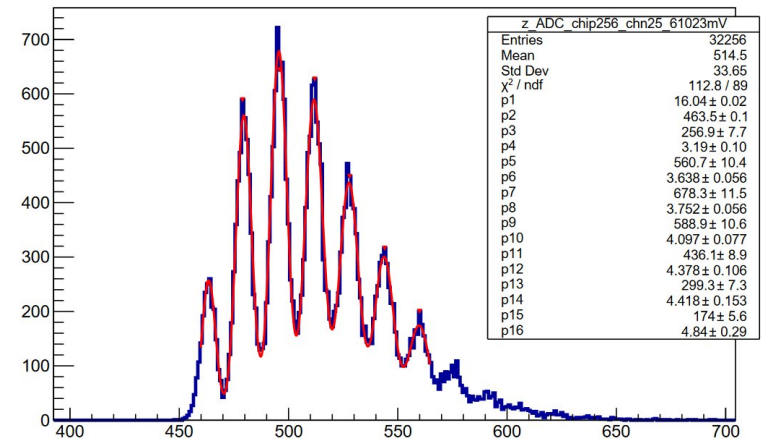
- 0.3 pixels (average value).
- estimated from the width of the pedestal (zeroth peak in LED measurements)

$$A^{sat}[pixels]_i = N_{effpixels} * (1 - \exp(-\frac{A^{nosat}[pixels]_i}{N_{effpixels}}))$$

Amplitude of the hit not saturated

Saturated amplitude of the hit

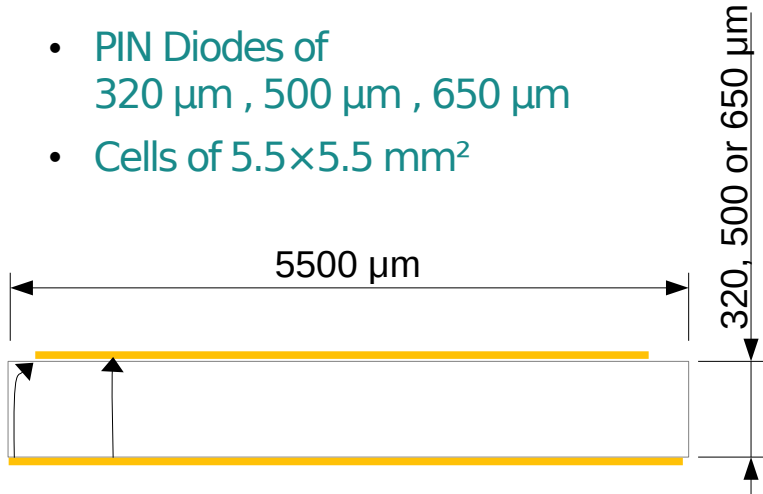
Number of effective pixels, which in our case is 2668 pixels



Silicon ECAL

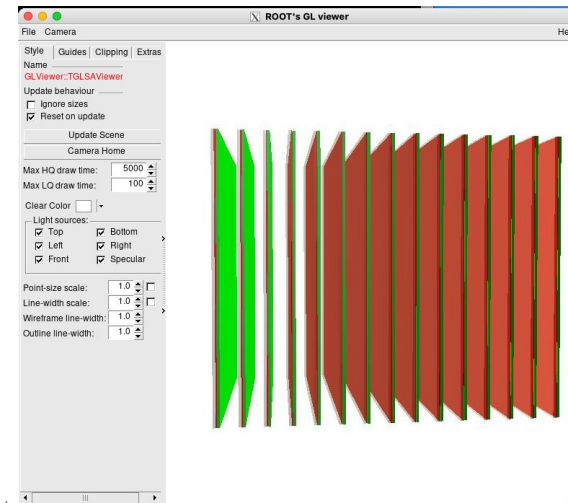
Prototype:

- 15 layers of $18 \times 18 \text{ cm}^2$
- Silicon sensors:
 - PIN Diodes of $320 \mu\text{m}$, $500 \mu\text{m}$, $650 \mu\text{m}$
 - Cells of $5.5 \times 5.5 \text{ mm}^2$

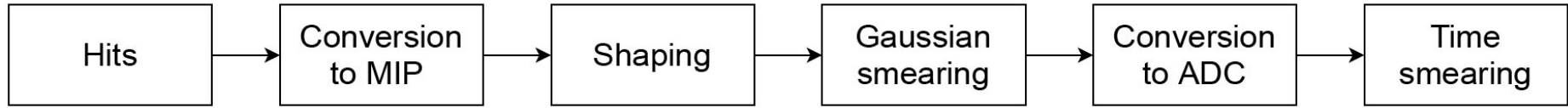


Simulation

- Gaps between wafers
- No-gaps between cells
 - Charge collections $\sim 100\%$
 - To be evaluated with dedicated simulation (GarField++, ...) and data

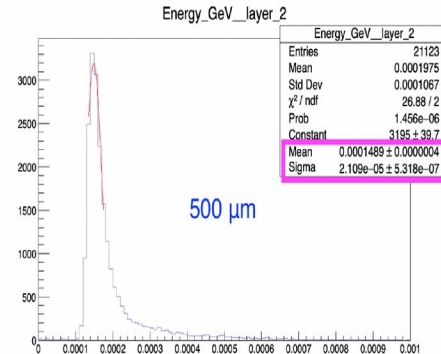
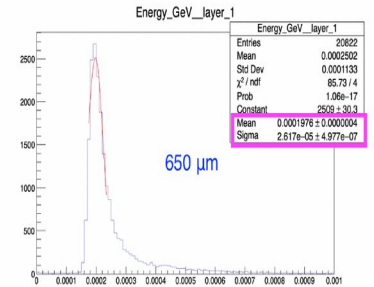
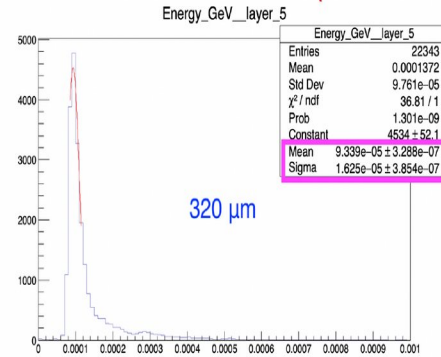


Silicon ECAL Digi



- Hits: starting point from raw simulation.
- Map energy deposited to MIP scale.

Conversion to MIP scale (electrons @ 3 GeV)



- Conversion per layer (different layers Si thickness)

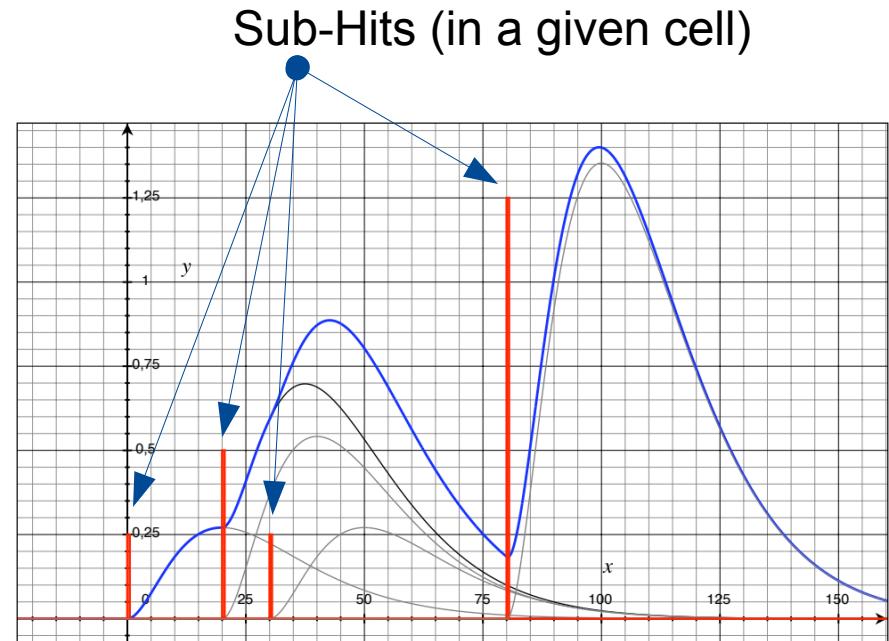
Pulse shaping

n^{th} order CR-RC filter

- Linear response to step function

$$s(t,A)=\begin{cases} 0 & x-t < 0 \\ \frac{A}{n!} \left(\frac{x-t}{\tau_i} \right)^n \exp\left(-\frac{x-t}{\tau_i}\right) & x-t > 0 \end{cases}$$

- Ignores exp. tail
- Ignores saturation effects ($\geq \sim 2000$ mips)



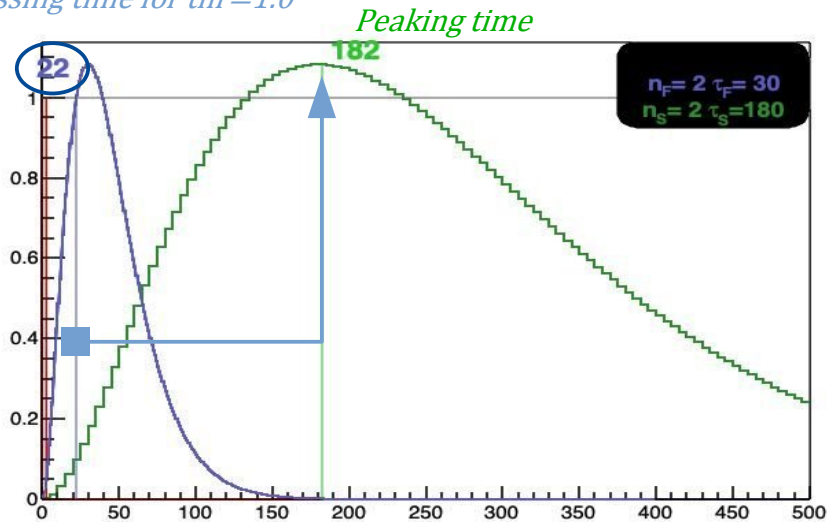
Example of pulse shape output of CR-(CR)² filter with a $n\tau=20$ ns from 4 inputs, at 0, 20, 30 and 80 ns, with relative amplitudes of 1, 2, 1 and 5.

Implementation for each channel

Shaping by histograms:

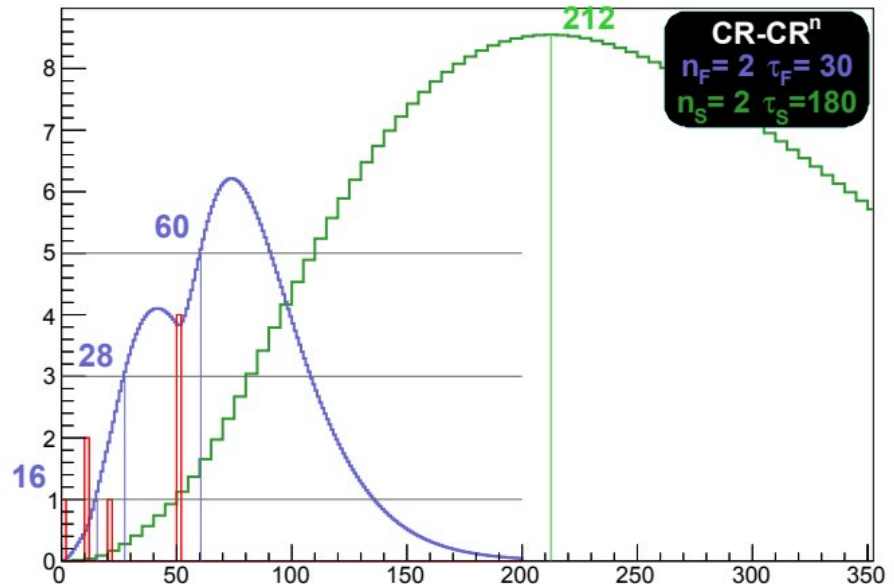
- bin \sim time resolution
 - 1 ns for FS
 - 5 ns for SS

Crossing time for $thr=1.0$



Multiple hits

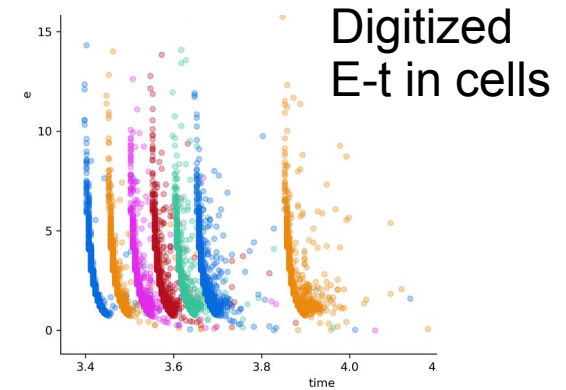
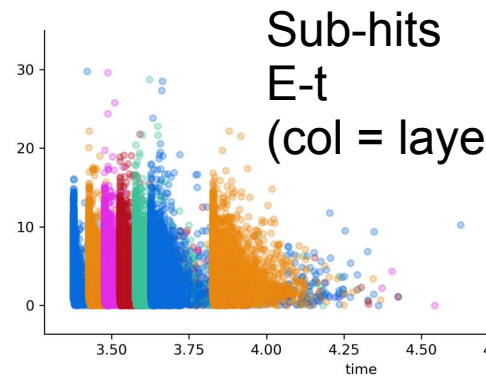
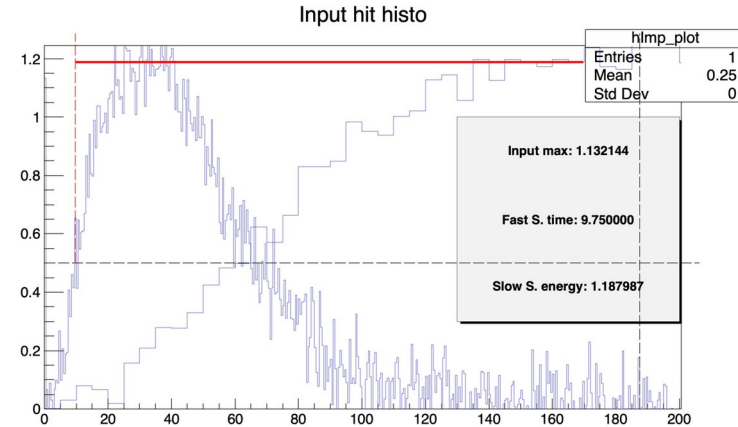
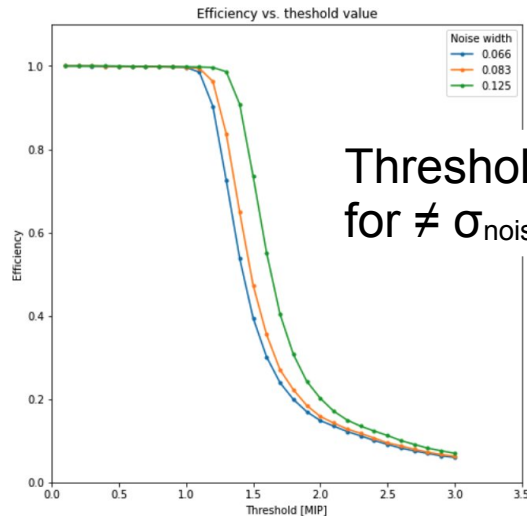
- Time slew effect
- Peaking time

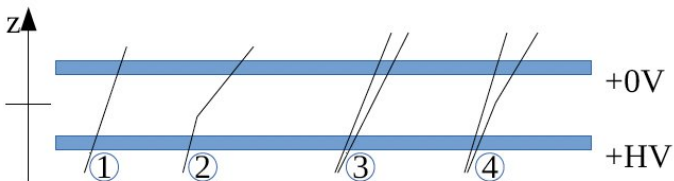


SiW-ECAL digitizer by shaping

SiW-ECAL digitizer by shaping

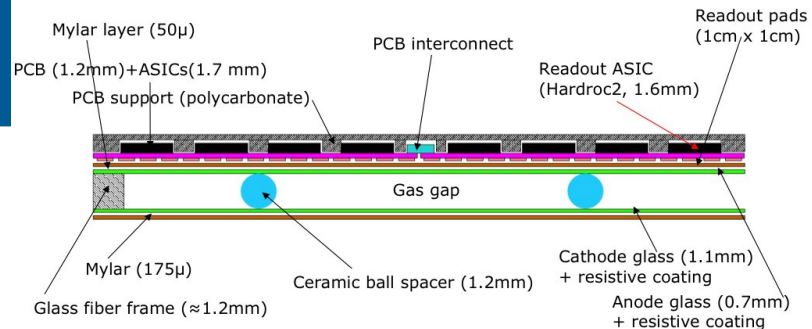
- Shaping processor properly implements noise and a realistic time binning
Example: Threshold 0.5 MIP, delay 180 ns
- Shapers with noise MIP/12 and MIP/20





Simulation output

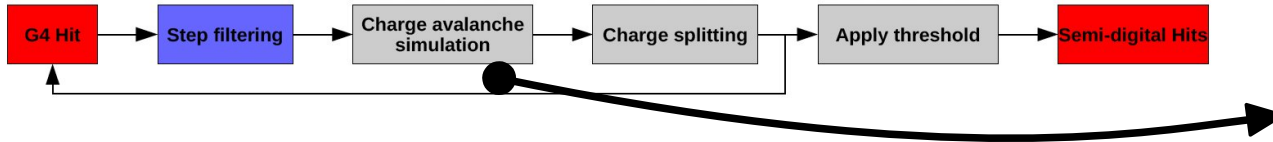
- steps list inside RPC gas gaps
- deposited energy from these steps
- occurrence time of each step
- entrance and exit point positions of each step



Glass resistive plate chambers

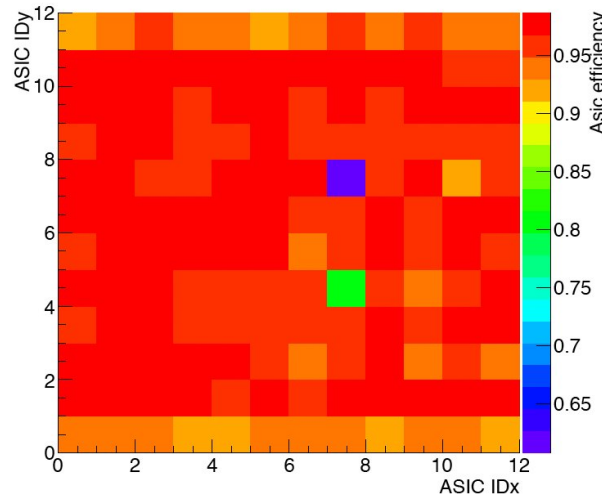
- Glass electrodes separated by 1.2 mm gas gap
- Glass resistivity $\approx 10^{12} \Omega m$
- Gas mixture : 93% TFE , 5% CO_2 , 2% SF_6
- High voltage : 6.9 kV \rightarrow avalanche mode
- Transverse segmentation : 1 cm^2
- Thresholds : 0.114, 5.0, 15.0 pC

Digitizer method



Step filtering

- Step occurrence time < 1000 ns
- Step length > 1 μm
- Efficiency map
- Charge screening (d_{cut} tuned with electromagnetic showers)



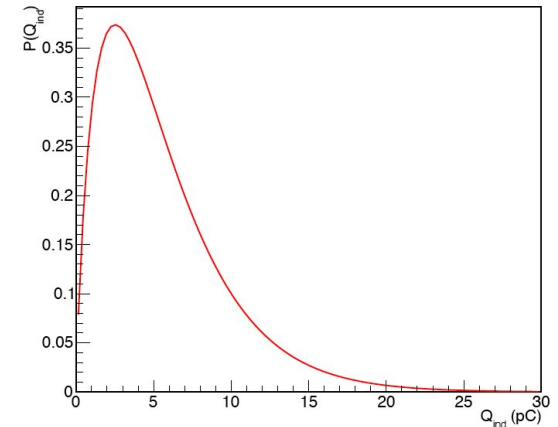
Charge avalanche simulation

- Charge randomly chosen in Polya distribution :

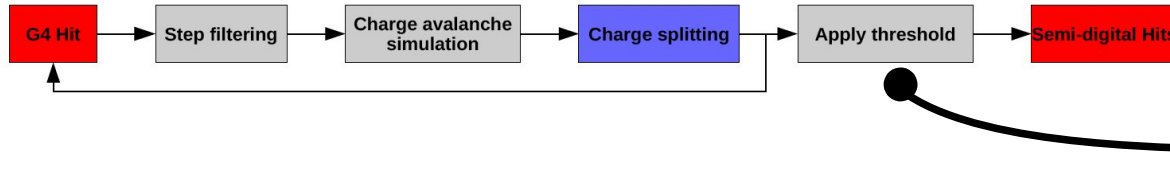
$$P(q) = \frac{1}{\Gamma(\delta + 1)} \left(\frac{1 + \delta}{\bar{q}} \right)^{\delta+1} q^{\delta} e^{-\frac{q}{\bar{q}}(1+\delta)}$$

- Length charge correction :

$$Q_{Corrected} = \begin{cases} Q_{ind} \left(\frac{d_s}{d_{gap}} \right)^{\kappa} & \text{if } \frac{d_s}{d_{gap}} > 1 \\ Q_{ind} & \text{otherwise} \end{cases}$$



SDHCAL Digi : Amplification



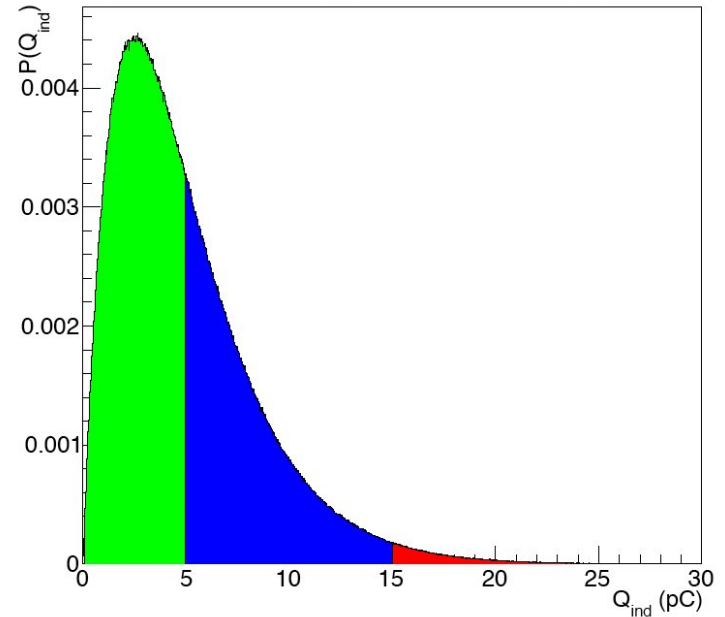
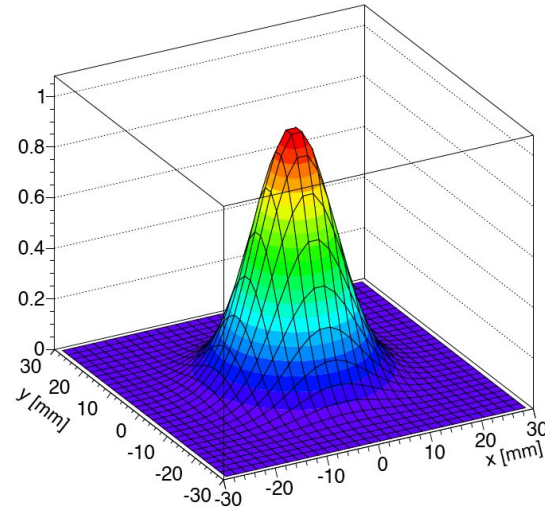
Thresholds

- Thresholds 2 and 3 tuned with muon data to reproduce efficiency related to threshold 2 and 3

Charge spreading

$$R_i = \frac{\int_{a_i}^{b_i} \int_{c_i}^{d_i} \sum_{j=0}^n \alpha_j e^{-\frac{(x_0-x)^2+(y_0-y)^2}{\sigma_j^2}} dx dy}{N}$$

- Charge in pad i incremented by $R_i Q_{corrected}$



SDHCAL Digi : Tuning

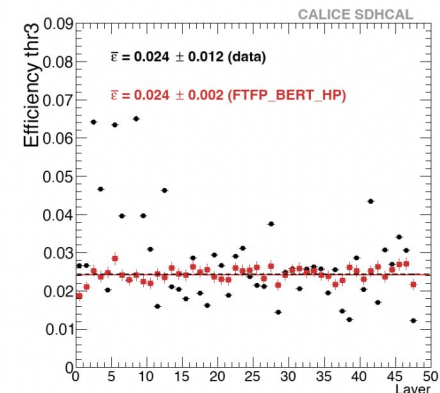
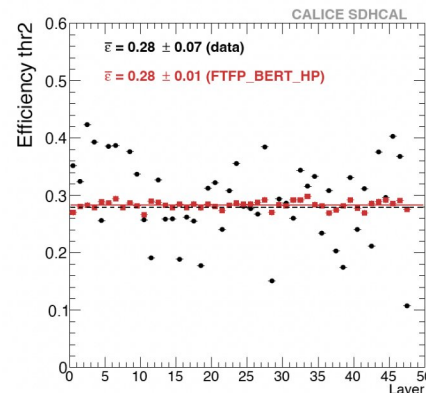
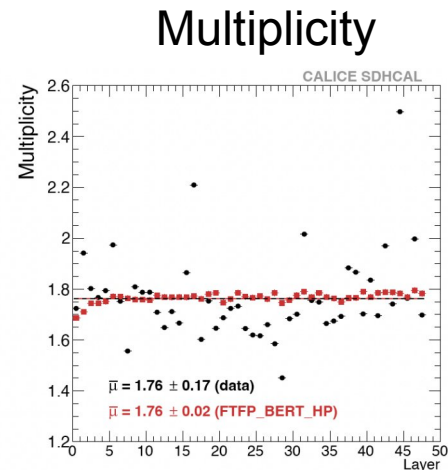
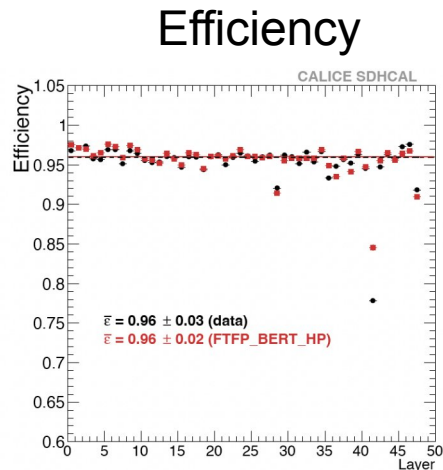
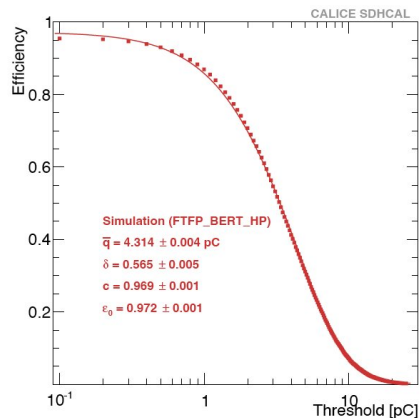
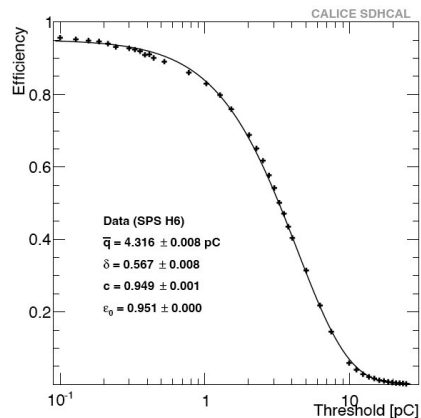
Digitizer parametrisation : threshold scan

Threshold scan method :

- ~ 20 dedicated muon runs
- Threshold variation in few chambers
- Efficiency reconstructed with tracks from other layers
- Fit the curve to extract \bar{q} and δ parameters

$$\epsilon(q) = \epsilon_0 - c \int_0^q P(q') dq'$$

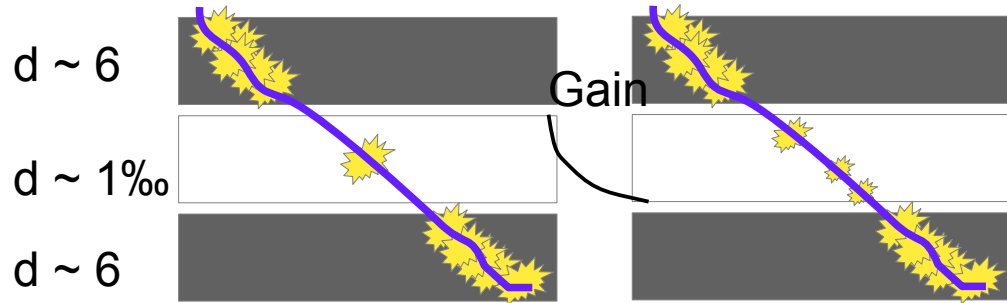
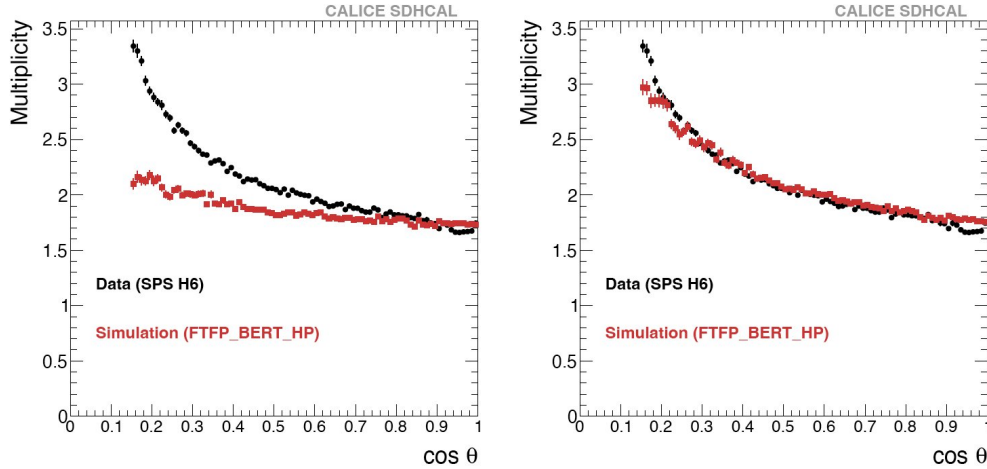
Polya parameter	Digitizer input value
\bar{q}	4.58 pC
δ	1.12



Lengthy dedicated BT μ runs with thr. scan

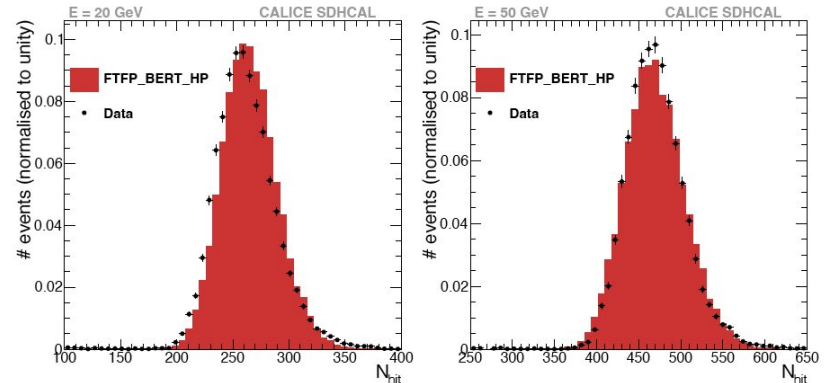
SDHCAL Digi: results

Improved parametrization & Step length



Electromagnetic showers

- Digitizer parameter tuned with EM showers (d_{cut})
- EM shower selection :
 $N_{tracks} = 0$ & $P_{start} < 5$ & $N_{layers} < 30$
- Selection efficiency $\geq 98\%$
- Relative deviation $< 3\%$



Comparison with Had. Shower complex:

- Clustering, Shower profiles, Beam contamination ...
- Physics list

Conclusions

Summary

- Digitization links MC to exp. Data
- Very sensor Specific
 - Silicon < Scint ≪ Gas RPC
 - Amplitude, Time
 - Geometry
- Electronics :
 - Standard: Gain,
 - Next / On-going precision timing
- Precision of description
 - Gaps, ineff. maps
- Only possible with (lot of) dedicated BT data

Big, Cursed & politically sensitive work

- The more advanced, the less performant
- Simplistic / Incomplete digitization yields better results... until compared with data !
 - Why invest ?

→ Technology comparisons review committee task must be done with prototypes & Sim+Digi.